MDG002R040SL

MOSFETs Silicon 40V N-Channel MOS

Applications

- Synchronus Rectification
- Industrial and Motor Drive
- DC/DC and AC/DC Converters
- Power Tools

Product Summary

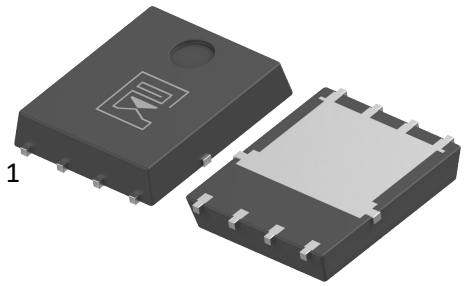
V_{DS}	40	V
I_D	156	A
$R_{DS(ON),Typ}$@10V	1.7	mΩ
$R_{DS(ON),Typ}$@4.5V	2.3	mΩ
Q_g	54	nC

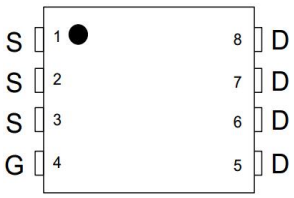
Features

- High-Speed Switching
- Low $R_{DS(ON)}$
- Enhanced Body diode dv/dt capability
- Enhanced Avalanche Ruggedness
- 100% UIS and RG Tested

RoHS Pb Lead-free HF

DFN5x6





Gate： 4
Drain： 5-8
Source： 1-3

Package Marking and Ordering Information

Ordering code	Marking	Package	Packaging	Min. package quantity
MDG002R040SL	MDG002R040SL	DFN5x6	Tape & Reel	5000

Absolute Maximum Ratings（Tc=25℃ unless otherwise noted)

Parameter			Symbol	Ratings	Unit
Drain-Source Voltage			V_{DS}	40	V
Gate-Source Voltage			V_{GS}	±20	V
Continuous Drain Current	Tc=25℃	(Note 1)	I_D	156	A
Continuous Drain Current	Tc=100℃	(Note 1)		100	A
Drain Current-Pulsed		(Note 1)	I_{DM}	600	A
Total Dissipation			P_D	73	W
Junction Temperature			T_j	150	℃
Storage Temperature			T_{stg}	-55-150	℃
Single Pulse Avalanche Energy		(Note 2)	E_{AS}	500	mJ

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Thermal Characteristics

Parameter	Symbol	Max	Unit
Maximum Junction-to-Case	$R_{\theta JC}$	1.7	℃/W
Maximum Junction-to-Ambient	$R_{\theta JA}$	60	℃/W

Note 1：Ensure that the channel temperature does not exceed 150℃.

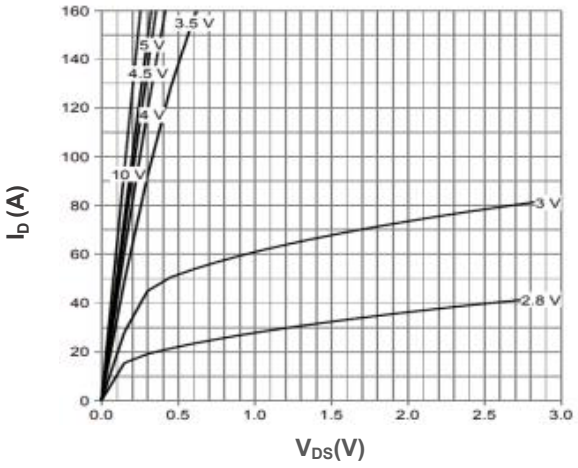
Note 2：V_{DD}=40V, Tch= 25℃(initial), L=0.5mH, Rg=25Ω.

Note：This transistor is sensitive to electrostatic discharge and should be handled with care.

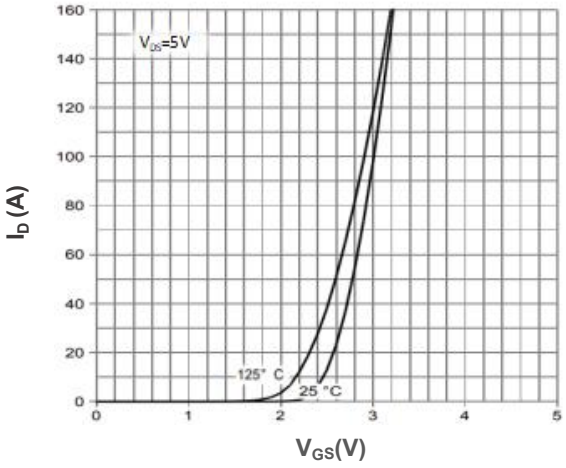
Electrical Characteristics（Tc=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Parameters						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250uA	40	-	-	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=40V,VGS=0V	-	-	1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS}=V_{DS},I_D=250uA	1.0	1.8	3.0	V
Drain-Source On Resistance	$R_{DS(ON)}$	V_{GS}=4.5V,I_D=15A	-	2.3	2.7	mΩ
		Tj=125℃	-	3.3	-	
		V_{GS}=10V,I_D=20A	-	1.7	2.0	mΩ
		Tj=125℃	-	2.4	-	
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=15V,V_{GS}=0V, f=1.0MHz	-	3348	-	pF
Output Capacitance	C_{oss}		-	2063	-	pF
Reverse Transfer Capacitance	C_{rss}		-	55	-	pF
Gate Resistance	R_g	V_{DS}=0V,V_{GS}=0V, f=1.0MHz	-	2.1	-	Ω
Switching Paramters						
Turn-On Delay Time	$t_{d(on)}$	V_{DS}=20V,I_D=20A, V_{GS}=10V,R_G=10Ω	-	28	-	ns
Turn-On Rise Time	t_r		-	15	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	75	-	ns
Turn-Off Rise Time	t_f		-	18	-	ns
Total Gate Charge	Q_g	V_{DS}=32V,I_D=20A, V_{GS}=10V	-	54	-	nC
Gate-Source Charge	Q_{gs}		-	10	-	nC
Gate-Drain Charge	Q_{gd}		-	11	-	nC
Source-Drain Characteristics						
Diode Forward Voltage	V_{sd}	V_{GS}=0V,I_S=10A	-	0.8	1.2	V
Reverse Recovery Time	t_{rr}	V_R=40V,I_F=20A, di/dt=100A/us	-	112	-	ns
Reverse Recovery Charge	Q_{rr}		-	190	-	nC

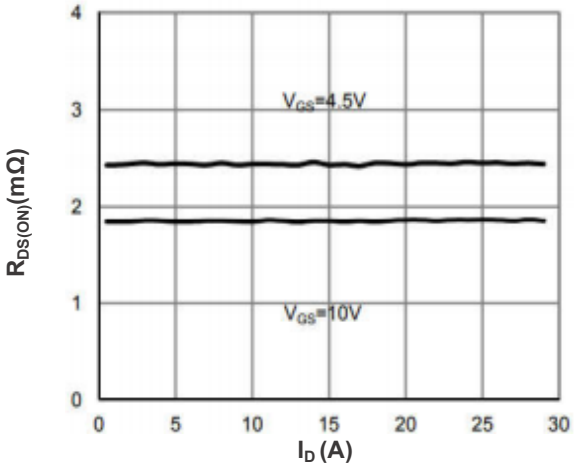
Characteristics Curves



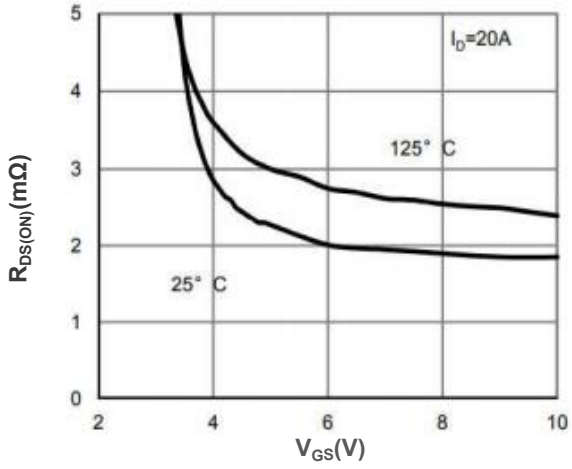
Output Characteritsics



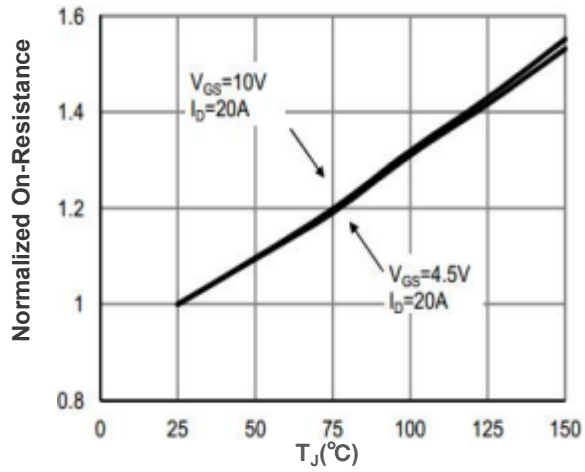
Transfer Characteritsics



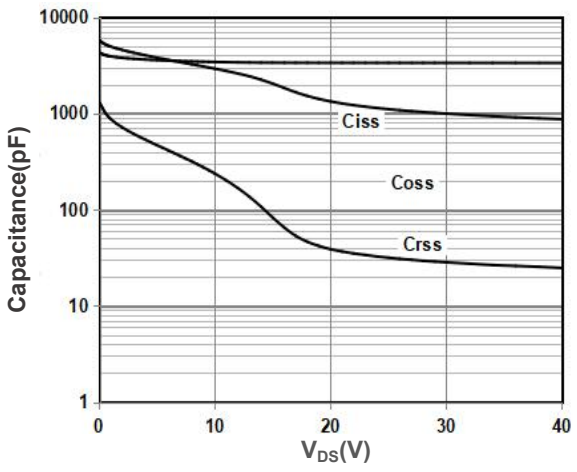
On Resistance Vs Drain Current



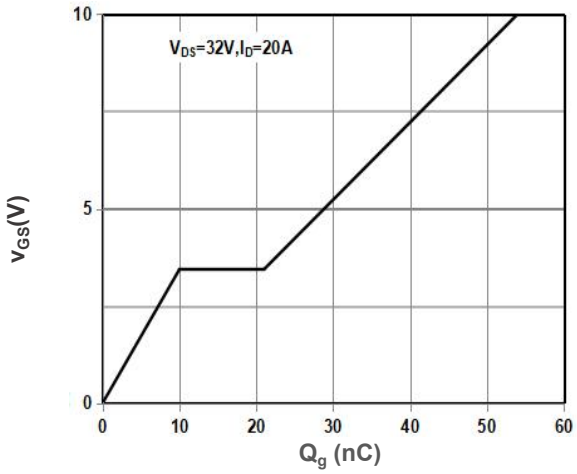
On Resistance Vs Gate Source Voltage



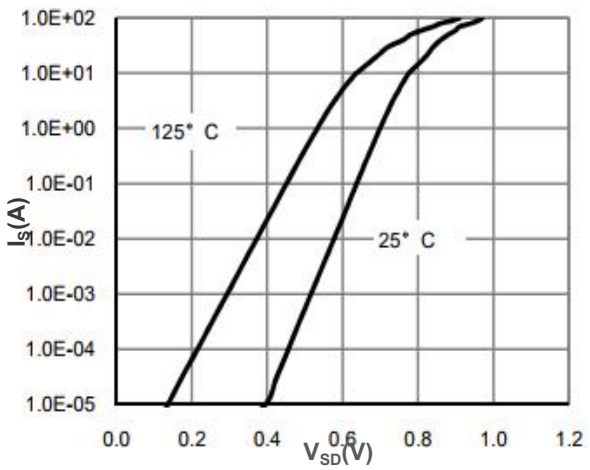
Rdson-JunctionTemperature



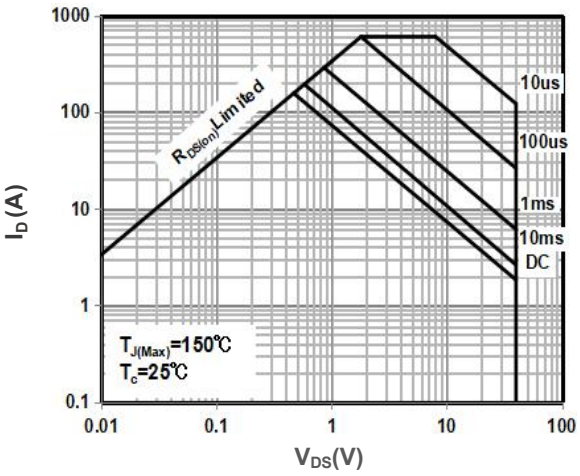
Capacitance



Gate Charge Waveform



Source-Drain Diode Forward Voltage

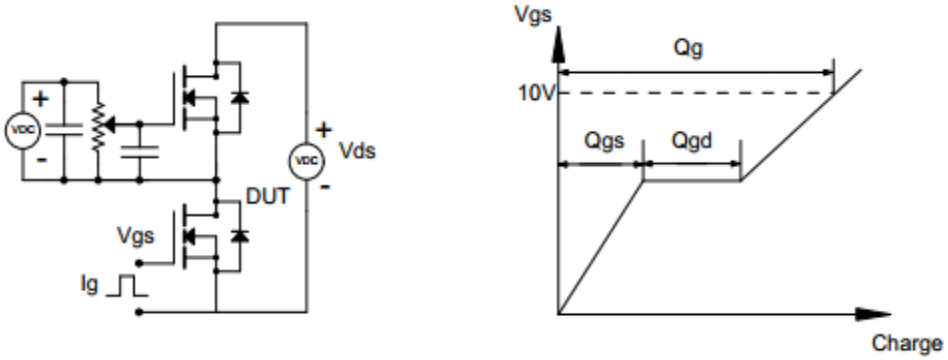


Maximum Safe Operating Area

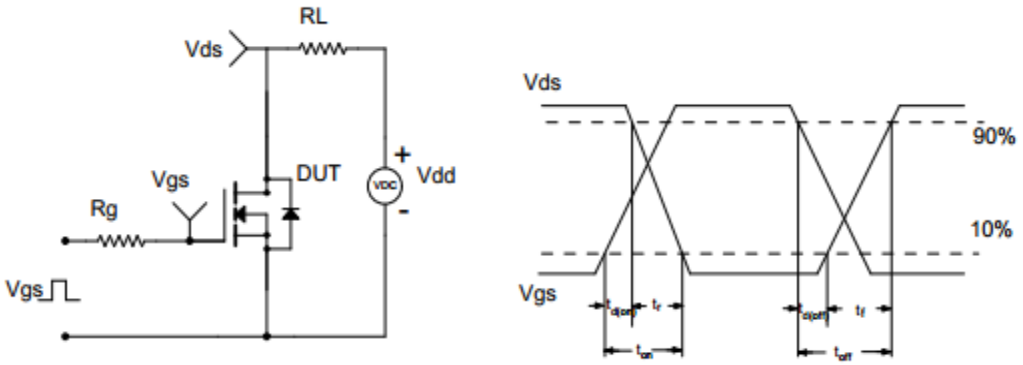
Note： The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Test Circuit & Waveform

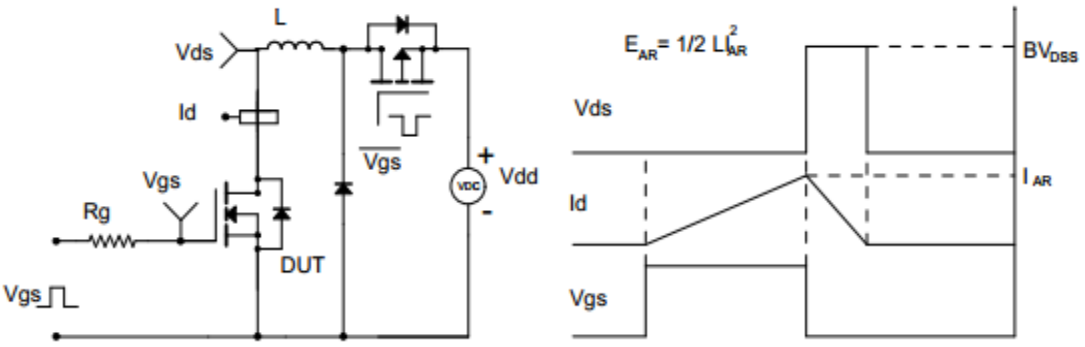
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveform



DFN5x6 Package Dimensions

Unit：mm

Symbol	Min	Nom	Max	Symbol	Min	Nom	Max
A	0.90		1.10	k	1.15		1.35
A3	0.15		0.30	b	0.20		0.40
D	4.90		5.10	e	1.15		1.35
D1	3.90		4.10	L	0.50		0.65
D2	4.75		5.05	L1	0.43		0.55
E	5.85		6.15	H	0.55		0.68
E1	3.35		3.55	θ	8°		12°
E2	5.55		5.85